NEW

TD•0062

Low power dual BI-FET operational amplifiers.

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The TD•0062, are high speed dual J-FET input operational amplifiers. Each of these incorporates well matched, high voltage J-FET and bipolar transistors in a monolithic integrated circuit.
The devices feature high slew rate, low input bias and offset currents, and low offset voltage temperature cœfficient.

- Very low power consumption.
- Wide common-mode and differential voltage ranges.
- Low input bias and offset currents.
- Typical supply current 200 μA.
- Output short-circuit protection.
- High impedance J-FET input stage.
- Internal frequency compensation.
- Latch-up free operation.
- High slew rate 3.5 V/μs typ.

BI-FET OPERATIONAL AMPLIFIERS

CHARACTERISTIC	SYMBOL	UNIT	SINGLE						DUAL				QUAD			
Supply voltage	V_{CC} max.	V	±18	±18	±18	±18	±18	±18	±18	±18	±18	±18	±18	±18	±18	±18
Input offset voltage	V_{IO}max.	mV	10	15	10	10	10	10	15	10	15	10	15	10	15	10
Input offset current	I_{IO}max.	nA	0.05	0.2	0.05	0.05	0.05	0.1	0.2	0.05	0.2	0.1	0.2	0.05	0.2	0.1
Input impedance	Z_I typ.	10^6MΩ	1	1	1	1	1	1	1	1	1	1	1	1	1	1
Input bias current	$I_B$max	nA	0.2	0.4	0.2	0.2	0.2	0.2	0.4	0.2	0.4	0.2	0.4	0.2	0.4	0.2
Slew rate	S_{VO}typ.	V/μs	13	13	5	12	50	13	3.5	13	13	13	3.5	13	13	13
Supply voltage rejection ratio	S_{VR}min.	dB	70	70	80	80	80	70	70	70	70	70	70	70	70	70
Gain ×bandwidth	B typ.	MHz	3	3	2.5	4.5	20	4	1	3	3	4	1	3	3	4
Voltage gain	$A_V$min.	V/mV	25	25	25	25	25	25	3	25	25	25	3	25	25	25
Input voltage range	($V_I$max.) min.	V	±11	±10	±10	±10	±10	±11	±10	±11	±10	±11	±10	±11	±10	±11

	TD•0071	TD•0081	TD•0155	TD•0156	TD•0157	TD•0351	TD•0062	TD•0072	TD•0082	TD•0353	TD•0064	TD•0074	TD•0084	TD•0347	
		⑧				⑧	⑧		⑧	⑧	⑭		⑭		Plastic SO 8-14
	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑧	⑭	⑭	⑭	⑭	Plastic DIL 8-14
											●	●	●		Cerdip DIL 14
		●	●						●				●		Chip carrier
	●		●	●	●	●		●		●					Metal can TO 99